

C750-55V

Infrared LED CHIP

<Specifications>

| Commodity Type and Physical Characteristics | |
|---------------------------------------------|--------------------|
| Material | GaAlAs/GaAlAs(DDH) |
| Top Side N(cathode)side | Au Alloy/Pad |
| Bottom Side P(anode)side | Au Alloy |
| Electrode Pattern | Fig.1 |
| Chip Size | Fig.2 |
| Chip Thickness | Fig.2 |
| Emission Area | Fig.2 |

| Electro-Optical Characteristics [Ta=25°C] | | | | | | |
|-------------------------------------------|-----------------|-----------|------|------|------|------|
| Item | Symbol | Condition | Min. | Typ. | Max. | Unit |
| Forward Voltage | Vf | IF=20mA | | 1.50 | 1.70 | V |
| Reverse Current | IR | VR=5V | | | 10 | uA |
| Power Intensity | PO | IF=20mA | 2.0 | 3.5 | | mW |
| Peak Wavelength | λP | IF=20mA | 740 | 750 | 760 | nm |
| Spectral Radiation Bandwidth | $\Delta\lambda$ | IF=20mA | | 30 | | nm |
| Rise Time | tr | IF=20mA | | 80 | | ns |
| Fall Time | tf | IF=20mA | | 80 | | ns |

Die shall be mounted on TO-18 gold header without resin coated.

[Unit:um]

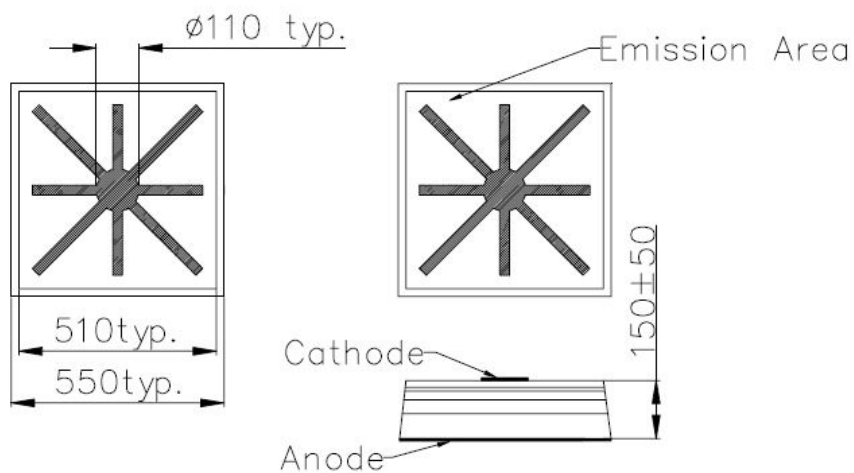


Fig.1 Electrode Pattern

Fig.2 Chip Size and Emission Area